

0910 - 60M

60 Watts - 40 Volts, 150µs, 5% Radar 890 - 1000 MHz

GENERAL DESCRIPTION

The 0910-60M is an internally matched, COMMON BASE transistor capable of providing 60 Watts of pulsed RF output power at 150 μs pulse width, 5% duty factor across the band 890 to 1000 MHz. This hermetically solder-sealed transistor is specifically designed for P-Band radar applications. It utilizes gold metallization to provide high reliability.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C 180 Watts

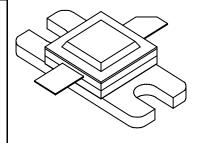
Maximum Voltage and Current

BVcesCollector to Emitter Voltage65 VoltsBVeboEmitter to Base Voltage3.5 VoltsIcCollector Current8 Amps

Maximum Temperatures

Storage Temperature $- 65 \text{ to} + 200^{\circ}\text{C}$ Operating Junction Temperature $+ 200^{\circ}\text{C}$

CASE OUTLINE 55AW-1



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pg ηc Pd Rl VSWR¹ VSWRs	Power Out Power Gain Collector Efficiency Pulse Droop Input Return loss Load Mismatch Tolerance Load Mismatch - Stability	Freq = 890 – 1000 MHz Vcc = 40 Volts Pin = 9.5 Watts Pulse Width = 150µs Duty Factor = 5%	60 8.0 40	8.5 45	84 0.5 3:1 2:1	Watts dB % dB dB

Note 1: Pulse condition of 150µsec, 5%.

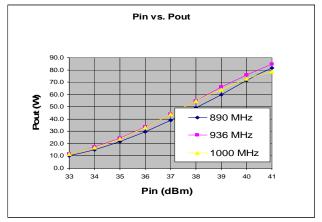
Bvces	Collector to Emitter Breakdown	Ic = 40 mA	65		Volts
Ices	Collector to Emitter Leakage	Vce = 40 Volts		10	mA
Iebo	Emitter to Base Leakage	Vebo = 3.0 Volts		8	mA
$\mathbf{\theta}\mathbf{jc}^{1}$	Thermal Resistance	Rated Pulse Condition		1.0	°C/W

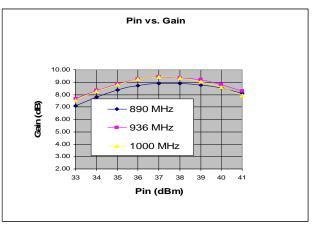
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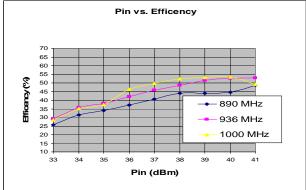


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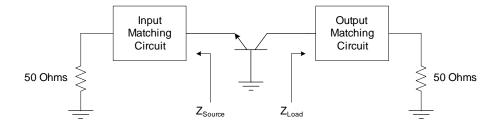
Performance Curves –







Impedance Information



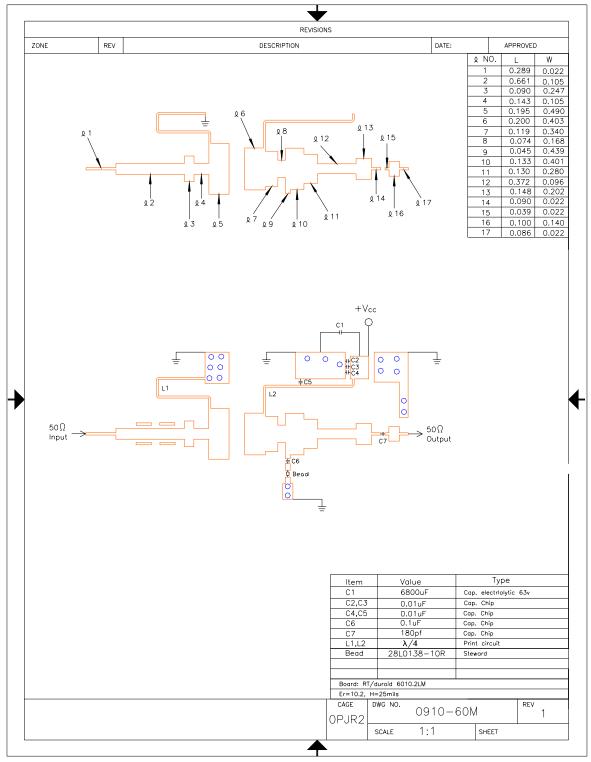
Frequencies (MHz)	$Z_{\scriptscriptstyle Source}(\Omega)$	$Z_{Load}(\Omega)^{2}$
890	4.4-j4.0	2.8-j0.7
937	4.5-j3.3	2.9-j0.0
1000	4.7-j2.5	3.2+j0.95

Note 2: Z_{Load} exclusive of C5, C6 and bead on the test circuit



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Test Circuit





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